Nadiia Korsunska

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| # | Paper | IF | Citations |
|-----|--|----------------|-----------|
| 133 | The influence of defect drift in external electric field on green luminescence of ZnO single crystals. <i>Journal of Luminescence</i> , 2003 , 102-103, 733-736 | 3.8 | 116 |
| 132 | Thermal activation of excitons in asymmetric InAs dots-in-a-well InxGa1🛭 As 🗓 aAs structures. Journal of Applied Physics, 2007 , 101, 024323 | 2.5 | 71 |
| 131 | Reversible and non-reversible photo-enhanced luminescence in CdSe/ZnS quantum dots. <i>Semiconductor Science and Technology</i> , 2005 , 20, 876-881 | 1.8 | 50 |
| 130 | The role of oxidation on porous silicon photoluminescence and its excitation. <i>Thin Solid Films</i> , 2001 , 381, 88-93 | 2.2 | 46 |
| 129 | Nature of visible luminescence and its excitation in SiBiOx systems. <i>Journal of Luminescence</i> , 2003 , 102-103, 705-711 | 3.8 | 43 |
| 128 | Photosensitivity degradation mechanism in CdS:Cu single crystals. <i>Physica Status Solidi A</i> , 1980 , 60, 565- | -572 | 40 |
| 127 | Ballistic effect in red photoluminescence of Si wires. <i>Physical Review B</i> , 2002 , 65, | 3.3 | 37 |
| 126 | The recharge-enhanced transformations of donor-acceptor pairs and clusters in CdS. <i>Journal of Physics and Chemistry of Solids</i> , 1982 , 43, 475-479 | 3.9 | 35 |
| 125 | Three approaches to surface substance role investigation in porous silicon photoluminescence and its excitation. <i>Journal of Physics and Chemistry of Solids</i> , 2000 , 61, 937-941 | 3.9 | 29 |
| 124 | Electrodiffusion of shallow donors in CdS crystals. <i>Journal of Physics C: Solid State Physics</i> , 1980 , 13, 297 | '5-297 | 8 29 |
| 123 | OH-related emitting centers in interface layer of porous silicon. <i>Physica B: Condensed Matter</i> , 1999 , 273-274, 955-958 | 2.8 | 28 |
| 122 | Defect-related luminescence of Si/SiO2layers. Journal of Physics Condensed Matter, 2002, 14, 13217-132 | 2 2 .18 | 25 |
| 121 | Complex nature of the red photoluminescence band and peculiarities of its excitation in porous silicon. <i>Applied Surface Science</i> , 2000 , 167, 197-204 | 6.7 | 25 |
| 120 | Radiative channel competition in silicon nanocrystallites. <i>Journal of Luminescence</i> , 2005 , 115, 117-121 | 3.8 | 24 |
| 119 | Enhancement of the photoluminescence in CdSe quantum dotpolyvinyl alcohol composite by light irradiation. <i>Applied Surface Science</i> , 2013 , 281, 118-122 | 6.7 | 19 |
| 118 | Suboxide-related centre as the source of the intense red luminescence of porous Si. <i>Microelectronic Engineering</i> , 2000 , 51-52, 485-493 | 2.5 | 16 |
| 117 | High-temperature photoluminescence spectroscopy in p-type SiC. <i>Semiconductor Science and Technology</i> , 2004 , 19, 833-838 | 1.8 | 14 |

(2017-2005)

| 116 | Raman scattering characterization of macro- and nanoporous silicon. <i>Applied Surface Science</i> , 2005 , 243, 30-35 | 6.7 | 13 |
|-----|--|------|----|
| 115 | COPROX reactions on copper Y2O3-ZrO2 catalysts prepared by a single step co-precipitation technique. <i>Applied Catalysis B: Environmental</i> , 2020 , 278, 119258 | 21.8 | 12 |
| 114 | Scanning photoluminescent spectroscopy of bioconjugated quantum dots. <i>Superlattices and Microstructures</i> , 2009 , 45, 240-248 | 2.8 | 11 |
| 113 | Nature of visible luminescence of co-sputtered SiBiOx systems. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 1119-1123 | 2.8 | 11 |
| 112 | Luminescence and EPR studies of defects in Si-SiO2films. <i>EPJ Applied Physics</i> , 2004 , 27, 285-287 | 1.1 | 11 |
| 111 | The effect of bio-conjugation on aging of the photoluminescence in CdSeTeInS coreIhell quantum dots. <i>Superlattices and Microstructures</i> , 2012 , 51, 353-362 | 2.8 | 10 |
| 110 | The influence of annealing on structural and photoluminescence properties of silicon-rich Al2O3 films prepared by co-sputtering. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2013 , 51, 115- | 119 | 10 |
| 109 | Role of paramagnetic defects in light emission processes in Y-doped ZrO2nanopowders. <i>Materials Research Express</i> , 2014 , 1, 045011 | 1.7 | 10 |
| 108 | Photoluminescence and EPR studies of porous silicon. <i>Journal of Luminescence</i> , 1997 , 72-74, 400-402 | 3.8 | 10 |
| 107 | Two ways of porous Si photoluminescence excitation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1998 , 51, 162-165 | 3.1 | 10 |
| 106 | Spectroscopic behavior of bioconjugated quantum dots. <i>Semiconductor Science and Technology</i> , 2008 , 23, 075045 | 1.8 | 10 |
| 105 | The effect of oxidation on the efficiency and spectrum of photoluminescence of porous silicon. <i>Semiconductors</i> , 2006 , 40, 598-604 | 0.7 | 10 |
| 104 | USXES AND OPTICAL PHENOMENA IN SI LOW-DIMENSIONAL STRUCTURES DEPENDENT ON MORPHOLOGY AND SILICON OXIDE COMPOSITION ON SI SURFACE. <i>Surface Review and Letters</i> , 2002 , 09, 1047-1052 | 1.1 | 10 |
| 103 | Photoluminescence, conductivity and structural study of terbium doped ZnO films grown on different substrates. <i>Materials Science in Semiconductor Processing</i> , 2019 , 94, 51-56 | 4.3 | 9 |
| 102 | Si-rich Al2O3 films grown by RF magnetron sputtering: structural and photoluminescence properties versus annealing treatment. <i>Nanoscale Research Letters</i> , 2013 , 8, 273 | 5 | 9 |
| 101 | The nature of emission of porous silicon produced by chemical etching. Semiconductors, 2010, 44, 79-83 | 0.7 | 9 |
| 100 | Mechanism of photoexcitation of oxide-related emission bands in SiBiO2 systems. <i>Materials Science and Engineering C</i> , 2003 , 23, 691-696 | 8.3 | 9 |
| 99 | Thermo-stimulated evolution of crystalline structure and dopant distribution in Cu-doped Y-stabilized ZrO2 nanopowders. <i>Materials Research Express</i> , 2017 , 4, 035024 | 1.7 | 8 |

| 98 | Impurity-Governed Modification of Optical and Structural Properties of ZrO-Based Composites Doped with Cu and Y. <i>Nanoscale Research Letters</i> , 2017 , 12, 157 | 5 | 8 |
|----|---|------|---|
| 97 | Nanostructured Y-doped ZrO2 powder: peculiarities of light emission under electron beam excitation. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014 , 11, 1417-1422 | | 8 |
| 96 | Structural and Luminescent Properties of (Y,Cu)-Codoped Zirconia Nanopowders. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, N103-N110 | 2 | 8 |
| 95 | About the origin of center responsible for Cu-related blue emission band in ZnS:Cu. <i>Journal of Luminescence</i> , 2014 , 145, 71-73 | 3.8 | 8 |
| 94 | The structure of SiBiO2 layers with high excess Si content prepared by magnetron sputtering. <i>Thin Solid Films</i> , 2009 , 517, 5468-5473 | 2.2 | 8 |
| 93 | Two sources of excitation of photoluminescence of porous silicon. <i>Semiconductors</i> , 1997 , 31, 773-776 | 0.7 | 8 |
| 92 | Depth redistribution of components of SiOx layers prepared by magnetron sputtering in the process of their decomposition. <i>Thin Solid Films</i> , 2007 , 515, 6749-6753 | 2.2 | 8 |
| 91 | A new type of structural defects in CdZnSe/ZnSe heterostructures. <i>Microelectronics Journal</i> , 2008 , 39, 589-593 | 1.8 | 8 |
| 90 | Investigation of aging process of SiBiOx structures with silicon quantum dots. <i>Journal of Applied Physics</i> , 2005 , 98, 113515 | 2.5 | 8 |
| 89 | Ultrasound Stimulated Defect Reactions in Semiconductors. <i>Solid State Phenomena</i> , 2001 , 85-86, 317-3 | 36.4 | 8 |
| 88 | Optical investigations of the influence of point defects on quantum dots in CdSe/ZnSe heterostructures. <i>Journal of Physics Condensed Matter</i> , 2002 , 14, 13375-13380 | 1.8 | 8 |
| 87 | Large CdS single crystals with a high optical strength. <i>Materials Science and Engineering B:</i> Solid-State Materials for Advanced Technology, 1995 , 34, 12-17 | 3.1 | 8 |
| 86 | Investigation of undoped and Tb-doped ZnO films on Al2O3 substrate by infrared reflection method. <i>Thin Solid Films</i> , 2019 , 673, 136-140 | 2.2 | 7 |
| 85 | Modification of the photoluminescence characteristics of CdZnTe/ZnTe QWs by CdTe monolayer film insertion. <i>Physica Status Solidi (B): Basic Research</i> , 2007 , 244, 1700-1705 | 1.3 | 7 |
| 84 | Effect of adsorption and desorption processes on photoluminescence excitation spectra of porous silicon. <i>Applied Surface Science</i> , 2000 , 166, 349-353 | 6.7 | 7 |
| 83 | Graded ZnS/ZnSxO1☑ heterostructures produced by oxidative photolysis of zinc sulfide: Structure, optical properties and photocatalytic evolution of molecular hydrogen. <i>Journal of Photochemistry and Photobiology A: Chemistry</i> , 2016 , 329, 213-220 | 4.7 | 7 |
| 82 | New insight on the interaction of self-activated and Mn-related emission centers in ZnS. Semiconductor Science and Technology, 2017 , 32, 025006 | 1.8 | 6 |
| 81 | Structural and optical properties of ZnS:Mn micro-powders, synthesized from the charge with a different Zn/S ratio. <i>Journal of Materials Science: Materials in Electronics</i> , 2017 , 28, 8569-8578 | 2.1 | 6 |

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| 80 | Features of ZnS-powder doping with a Mn impurity during synthesis and subsequent annealing. <i>Semiconductors</i> , 2013 , 47, 713-720 | 0.7 | 6 |
|----|---|-----|---|
| 79 | Effect of conjugation with biomolecules on photoluminescence and structural characteristics of CdSe/ZnS quantum dots. <i>Semiconductors</i> , 2009 , 43, 775-781 | 0.7 | 6 |
| 78 | Redistribution of mobile point defects in CdS crystals under ultrasound treatment. <i>Physica B: Condensed Matter</i> , 2003 , 340-342, 258-262 | 2.8 | 6 |
| 77 | Redistribution of Tb and Eu ions in ZnO films grown on different substrates under thermal annealing and its impact on Tb-Eu energy transfer. <i>Applied Surface Science</i> , 2020 , 528, 146913 | 6.7 | 5 |
| 76 | The mechanism of formation of interface barriers in ZnO:Mn ceramics. SN Applied Sciences, 2020, 2, 1 | 1.8 | 5 |
| 75 | The mechanism of the photoluminescence changes in bio-conjugated CdSe/ZnS quantum dots. <i>Applied Surface Science</i> , 2013 , 281, 79-83 | 6.7 | 5 |
| 74 | Structural and light emission properties of silicon-based nanostructures with high excess silicon content. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2009 , 41, 1015-1018 | 3 | 5 |
| 73 | Some Peculiarities of Impurity Diffusion in CdS Crystals. <i>Physica Status Solidi (B): Basic Research</i> , 2002 , 229, 269-273 | 1.3 | 5 |
| 72 | Investigation of lattice defects by means of their drift under electric field. <i>Physica B: Condensed Matter</i> , 2001 , 308-310, 967-970 | 2.8 | 5 |
| 71 | The peculiarities of structural and optical properties of HfO2-based films co-doped with silicon and erbium. <i>Applied Surface Science</i> , 2019 , 471, 521-527 | 6.7 | 5 |
| 70 | Transformations in the photoluminescent, electrical and structural properties of Tb3+ and Eu3+ co-doped ZnO films under high-temperature annealing. <i>Journal of Luminescence</i> , 2020 , 217, 116739 | 3.8 | 5 |
| 69 | Grains, grain boundaries and total ionic conductivity of 10Sc1CeSZ and 8YSZ solid electrolytes affected by crystalline structure and dopant content. <i>Materials Today: Proceedings</i> , 2019 , 6, 79-85 | 1.4 | 4 |
| 68 | Formation of Cu-related emission centers under thermal doping of ZnS powders with CuCl and CuCl2. <i>Journal of Luminescence</i> , 2015 , 165, 94-98 | 3.8 | 4 |
| 67 | Peculiarities of Thermally Activated Migration of Subvalent Impurities in Cu-Doped Y-Stabilized ZrO2 Nanopowders Produced From Zr Oxychlorides. <i>Frontiers in Materials</i> , 2018 , 5, | 4 | 4 |
| 66 | Correlation between luminescent characteristics and phase composition of ZnS:Cu powder prepared by self-propagating high temperature synthesis. <i>Journal of Luminescence</i> , 2014 , 145, 970-975 | 3.8 | 4 |
| 65 | Modification by thermal annealing of the luminescent characteristics of CdSe quantum dots in gelatin films. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2012 , 9, 1779-1782 | | 4 |
| 64 | Structural and luminescent characteristics of macro porous silicon. <i>Journal of Materials Science: Materials in Electronics</i> , 2009 , 20, 226-229 | 2.1 | 4 |
| 63 | Growth peculiarities of silicon nanoparticles in an oxide matrix prepared by magnetron sputtering. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007 , 4, 3061-3065 | | 4 |

| 62 | Effect of CdTe monolayer insertion on CdZnTe/ZnTe quantum well characteristics. <i>Microelectronics Journal</i> , 2008 , 39, 418-422 | 1.8 | 4 |
|----|---|------|---|
| 61 | The interrelation of surface relief of porous silicon with specific features of Raman spectra. <i>Semiconductors</i> , 2002 , 36, 558-563 | 0.7 | 4 |
| 60 | Anti-Stokes photoluminescence and structural defects in CdSe/ZnSe nanostructures. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2003 , 101, 255-258 | 3.1 | 4 |
| 59 | Excitation mechanism of porous silicon luminescence: the role of sensitizers. <i>Thin Solid Films</i> , 1995 , 255, 185-187 | 2.2 | 4 |
| 58 | Point defect formation in IIIVI semiconductors at pulsed laser irradiation. <i>Journal of Crystal Growth</i> , 1990 , 101, 285-288 | 1.6 | 4 |
| 57 | Optical and Electrical Properties of TbInO/SiO2 Structure in the Infrared Spectral Interval. <i>Ukrainian Journal of Physics</i> , 2019 , 64, 434 | 0.4 | 4 |
| 56 | Structural and Optical Characterization of ZrO2 and Y2O3-ZrO2 Nanopowders 2015 , 59-67 | | 3 |
| 55 | Effect of Cu- and Y-Codoping on Structural and Luminescent Properties of Zirconia Based Nanopowders. <i>ECS Transactions</i> , 2015 , 66, 313-319 | 1 | 3 |
| 54 | Optical, structural and electrical characterization of pure ZnO films grown on p-type Si substrates by radiofrequency magnetron sputtering in different atmospheres. <i>Semiconductor Science and Technology</i> , 2020 , 35, 095034 | 1.8 | 3 |
| 53 | Structure and light emission of Si-rich Al2O3 and Si-rich-SiO2 nanocomposites. <i>Microelectronic Engineering</i> , 2014 , 125, 62-67 | 2.5 | 3 |
| 52 | Structure and Optical Properties of Magnetron Sputtered SiOx Layers with Silicon Nanoparticles. <i>Defect and Diffusion Forum</i> , 2008 , 272, 87-98 | 0.7 | 3 |
| 51 | Effect of growth temperature on the luminescent and structural properties of InGaAsSbN/GaAs quantum wells for 1.3 fb telecom application. <i>Thin Solid Films</i> , 2006 , 515, 786-789 | 2.2 | 3 |
| 50 | Study of strain relaxation in CdSe/ZnSe nanostructures. <i>Journal of Crystal Growth</i> , 2005 , 275, e2281-e2 | 2876 | 3 |
| 49 | Stability of Emission Properties of Silicon Nanostructures. <i>Solid State Phenomena</i> , 2005 , 108-109, 59-64 | 0.4 | 3 |
| 48 | Laser-Induced Defect Formation in ZnxCd1⊠Se Solid Solutions and Its Influence on Electrophysical Properties. <i>Physica Status Solidi A</i> , 1991 , 125, 127-132 | | 3 |
| 47 | The influence of carrier trapping on defect reaction activation energy in semiconductors (pseudo-effect of recombination enhanced diffusion). <i>Journal of Physics and Chemistry of Solids</i> , 1992 , 53, 469-474 | 3.9 | 3 |
| 46 | Silicon nanocrystals embedded in oxide films grown by magnetron sputtering. <i>AIMS Materials Science</i> , 2016 , 3, 538-561 | 1.9 | 3 |
| 45 | Thermally Stimulated Evolution of Optical and Structural Properties of Germanium-Doped Alumina Films. <i>ECS Transactions</i> , 2020 , 97, 81-90 | 1 | 2 |

| 44 | Mechanisms of the degradation of Schottky-barrier photodiodes based on ZnS single crystals. <i>Semiconductors</i> , 2016 , 50, 112-119 | 0.7 | 2 | |
|----|--|--------------------------|---|--|
| 43 | Photoluminescence and structural properties of CdSe quantum dot <code>g</code> elatin composite films. <i>Physica B: Condensed Matter</i> , 2014 , 453, 86-91 | 2.8 | 2 | |
| 42 | Study of thermal stability of CdSe/ZnSe quantum dot heterostructures. <i>Physica Status Solidi C:</i> Current Topics in Solid State Physics, 2012 , 9, 1768-1771 | | 2 | |
| 41 | Structural transformations in ZnS:Cu in the course of thermal annealing. <i>Semiconductors</i> , 2012 , 46, 188- | -1 <i>9.2</i> | 2 | |
| 40 | The peculiarities of Si/SiO2 interfaces in the SiBiO2 systems with Si nanocrystals. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2010 , 174, 97-101 | 3.1 | 2 | |
| 39 | Investigation of defect structure of InGaNAsSb/GaAs quantum wells. <i>Materials Science and Engineering C</i> , 2007 , 27, 1038-1042 | 8.3 | 2 | |
| 38 | Investigation of inhomogeneous broadening of CdSe/ZnSe nanoisland photoluminescence band by resonant excitation methods. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003 , 17, 93-94 | 3 | 2 | |
| 37 | Defect and nano-crystallite photoluminescence in Si-SiOx systems. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 2990-2993 | | 2 | |
| 36 | Optical characterization of CdZnTe/ZnTe heterostructures modified by electron or X-ray irradiation. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2001 , 80, 193-196 | 3.1 | 2 | |
| 35 | Lateral and depth inhomogeneities in Zn-based heterostructures grown on GaAs by MBE. <i>Thin Solid Films</i> , 2000 , 367, 184-188 | 2.2 | 2 | |
| 34 | Influence of annealing on photoinduced phenomena in CdS. <i>Journal Physics D: Applied Physics</i> , 1985 , 18, 677-683 | 3 | 2 | |
| 33 | Some peculiarities of thermostimulated conductivity and optical quenching of the photocurrent in crystals with the auger excitation of recombination centres. <i>Physica Status Solidi A</i> , 1978 , 50, 767-770 | | 2 | |
| 32 | Effect of Cooling Rate on Dopant Spatial Localization and Phase Transformation in Cu-Doped Y-Stabilized ZrO 2 Nanopowders. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2017 , 14, 1700183 | | 2 | |
| 31 | Effect of plasmonBhonon interaction on the infrared reflection spectra of MgxZn1-xO/Al2O3 structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2020 , 31, 7539-7546 | 2.1 | 1 | |
| 30 | Competition of the self-activated and Mn-related luminescence in ZnS single crystals. <i>Solid State Communications</i> , 2018 , 274, 31-35 | 1.6 | 1 | |
| 29 | The peculiarities of light absorption and light emission in Cu-doped Y-stabilized ZrO2 nanopowders. <i>Applied Nanoscience (Switzerland)</i> , 2019 , 9, 965-973 | 3.3 | 1 | |
| 28 | Micro-Raman and micro-photoluminescence study of bio-conjugated coreShell CdSe/ZnS nanocrystals. <i>Physica B: Condensed Matter</i> , 2014 , 453, 75-80 | 2.8 | 1 | |
| 27 | Comparative Investigation of Structural and Optical Properties of Si-Rich Oxide Films Fabricated by Magnetron Sputtering. <i>Advanced Materials Research</i> , 2013 , 854, 117-124 | 0.5 | 1 | |

| 26 | Interrelation between Light Emitting and Structural Properties of Si Nanoclusters Embedded in SiO2 and Al2O3 Hosts. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1617, 75-80 | | 1 |
|----|--|-----|---|
| 25 | Peculiarities of the thermal activation of carriers in CdSe/ZnSe QD structures. <i>Journal of Materials Science: Materials in Electronics</i> , 2009 , 20, 102-106 | 2.1 | 1 |
| 24 | Si-rich-SiO2 layers with high excess silicon content: Light emission and structural properties. <i>Physics Procedia</i> , 2009 , 2, 147-159 | | 1 |
| 23 | Effect of Various Treatments on Light Emission Properties of Si-Rich-SiOx Structures. <i>Solid State Phenomena</i> , 2007 , 131-133, 65-70 | 0.4 | 1 |
| 22 | Role of Cation Vacancy-Related Defects in Self-Assembling of CdSe Quantum Dots. <i>Defect and Diffusion Forum</i> , 2004 , 230-232, 55-66 | 0.7 | 1 |
| 21 | Investigation of intrinsic defects and their distribution in CdSe/ZnSe quantum dot structures. <i>Materials Science and Engineering C</i> , 2003 , 23, 715-719 | 8.3 | 1 |
| 20 | Spectroscopic characterization of phase transformation in Ge-rich Al2O3 films grown by magnetron co-sputtering. <i>Materials Letters</i> , 2020 , 277, 128306 | 3.3 | 1 |
| 19 | Transformation of excitonic and DA luminescence spectra of GaP:N light-emitting structures on the introduction of dislocations. <i>Semiconductor Science and Technology</i> , 1992 , 7, 385-390 | 1.8 | O |
| 18 | Phonon-Polariton Excitations in MgZnO/6H-SiC Structures. <i>Ukrainian Journal of Physics</i> , 2020 , 65, 162 | 0.4 | О |
| 17 | Mn Distribution in ZnO:Mn Ceramics: Influence of Sintering Process and Thermal Annealing. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 103001 | 2 | O |
| 16 | New Paramagnetic Center in Cu-Doped Y-Stabilized ZrO2. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 033002 | 2 | |
| 15 | Effects of Bio-conjugation and Annealing on the Photoluminescence and Raman Spectra of CdSe/ZnS Quantum Dots. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1534, A113-A119 | | |
| 14 | Photoinduced Photoluminescence Enhancement in CdSe Quantum Dot [Polyvinyl Alcohol Composites. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1534, A145-A150 | | |
| 13 | Photoluminescence and Structural Properties of CdSe Quantum Dot-Polymer Composite Films. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1617, 171-177 | | |
| 12 | Micro-Photoluminescence Study of Bio-conjugated CdSe/ZnS Nanocrystals. <i>Materials Research Society Symposia Proceedings</i> , 2013 , 1617, 157-162 | | |
| 11 | Structure and Optical Properties of Magnetron-Sputtered SiOx Layers with Silicon Nanoparticles. <i>Defect and Diffusion Forum</i> , 2010 , 303-304, 7-19 | 0.7 | |
| 10 | Study of the layer-substrate interface in nc-Si-SiO2-p-Si structures with silicon quantum dots by the method of temperature dependences of photovoltage. <i>Semiconductors</i> , 2010 , 44, 1187-1191 | 0.7 | |
| 9 | Biologically Engineered Quantum Dots for Biomedical Applications. <i>Materials Research Society Symposia Proceedings</i> , 2008 , 1095, 80501 | | |

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| 8 | Effect of structural imperfections on luminescence of ZnCdSe/ZnSe quantum wells. <i>Journal of Alloys and Compounds</i> , 2004 , 371, 202-205 | 5.7 |
|---|---|-----|
| 7 | Temperature activated 1.2 eV photoluminescence in semi-insulating SiC wafers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2005 , 2, 1892-1896 | |
| 6 | Influence of Different Atmospheres on the Life Time of Porous Silicon Light-Emitting Devices. <i>Materials Research Society Symposia Proceedings</i> , 2002 , 737, 665 | |
| 5 | Emission associated with extended defects in epitaxial ZnTe/GaAs layers and multilayer structures. <i>Semiconductors</i> , 2000 , 34, 11-16 | 0.7 |
| 4 | Features of the long-term photo emf relaxation in a heteroepitaxial ZnSe-GaAs structure. <i>Technical Physics Letters</i> , 2000 , 26, 190-192 | 0.7 |
| 3 | Generation of metastable shallow donors induced by cooling in hexagonal II-VI semiconductors. <i>Semiconductor Science and Technology</i> , 1992 , 7, 92-96 | 1.8 |
| 2 | Transformation of exciton and donor-acceptor luminescence spectra of p+-layers of gallium phosphide light-emitting structures on introduction of dislocations. <i>Journal of Applied Spectroscopy</i> , 1990 , 53, 1161-1166 | 0.7 |
| 1 | Alteration of the luminescence spectra of sintered layers of CdS:Cu:Cl due to photostimulated processes. <i>Journal of Applied Spectroscopy</i> , 1981 , 35, 1101-1103 | 0.7 |